



Not for new design, this product will be obsoleted soon

TSDF02424X/TSDF02424XR

Vishay Semiconductors

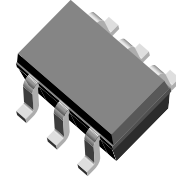
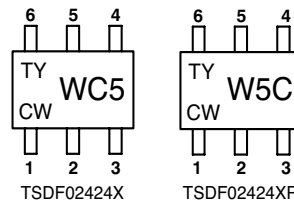
Dual - MOSMIC[®]- two AGC Amplifiers for TV-Tuner Prestage with 5 V Supply Voltage

Comments

MOSMIC - MOS Monolithic Integrated Circuit

Features

- Two AGC amplifiers in a single package
- Easy Gate 1 switch-off with PNP switching transistors inside PLL
- Integrated gate protection diodes
- Low noise figure
- High gain, medium forward transadmittance (24 mS typ.)
- Biasing network on chip
- Improved cross modulation at gain reduction
- High AGC-range with less steep slope
- SMD package, reverse pinning possible
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Electrostatic sensitive device. Observe precautions for handling.

16602

Mechanical Data

Typ: TSDF02424X

Case: SOT-363 Plastic case

Weight: approx. 6.0 mg

Pinning: 1 = Gate 1 (amplifier 1), 2 = Gate 2, 3 = Drain (amplifier 1), 4 = Drain (amplifier 2), 5 = Source, 6 = Gate1 (amplifier 2)

Typ: TSDF02424XR

Case: SOT-363 Plastic case

Weight: approx. 6.0 mg

Pinning: 1 = Gate 1 (amplifier 1), 2 = Source, 3 = Drain (amplifier 1), 4 = Drain (amplifier 2), 5 = Gate 2, 6 = Gate1 (amplifier 2)

V - Vishay

Y - Year, is variable for digit from 0 to 9 (e.g. 0 = 2000, 1 = 2001)

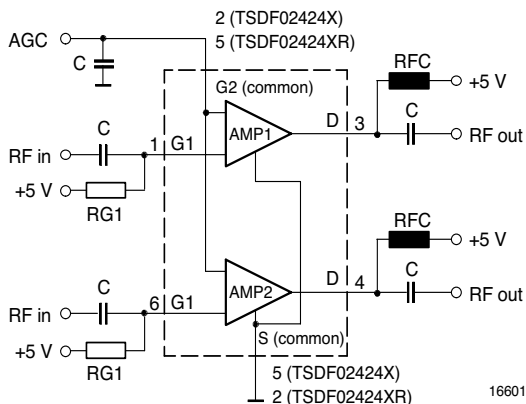
CW - Calendar Week, is variable for number from 01 to 52

Number of Calendar Week is always indicating place of pin 1

Applications

Low noise gain controlled input stages in UHF-and VHF- tuner with 5 V supply voltage.

Typical Application



Parts Table

| Part | Marking | Package |
|-------------|---------|----------|
| TSDF02424X | WC5 | SOT-363 |
| TSDF02424XR | W5C | SOT-363R |

All of following data and characteristics are valid for operating either amplifier 1 (pin 1, 3, 2, 5) or amplifier 2 (pin 6, 4, 2, 5)

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Value | Unit |
|-------------------------------------|---|---------------------|---------------|--------------------|
| Drain - source voltage | | V_{DS} | 8 | V |
| Drain current | | I_D | 25 | mA |
| Gate 1/Gate 2 - source peak current | | $\pm I_{G1/G2SM}$ | 10 | mA |
| Gate 1/Gate 2 - source voltage | | $+ V_{G1/\pm G2SM}$ | 6 | V |
| | | $- V_{G1SM}$ | 1.5 | V |
| Total power dissipation | $T_{amb} \leq 60\text{ }^{\circ}\text{C}$ | P_{tot} | 160 | mW |
| Channel temperature | | T_{Ch} | 150 | $^{\circ}\text{C}$ |
| Storage temperature range | | T_{stg} | - 55 to + 150 | $^{\circ}\text{C}$ |

Maximum Thermal Resistance

| Parameter | Test condition | Symbol | Value | Unit |
|-----------------|----------------|-------------|-------|------|
| Channel ambient | 1) | R_{thChA} | 450 | K/W |

1) on glass fibre printed board (25 x 20 x 1.5) mm³ plated with 35 μm Cu

Electrical DC Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|-----------------------------------|---|--------------------|-----|------|-----|------|
| Drain - source breakdown voltage | $I_D = 10\text{ }\mu\text{A}$, $V_{G1S} = V_{G2S} = 0$ | $V_{(BR)DSS}$ | 12 | | | V |
| Gate 1 - source breakdown voltage | $+ I_{G1S} = 10\text{ mA}$, $V_{G2S} = V_{DS} = 0$ | $+ V_{(BR)G1SS}$ | 7 | | 10 | V |
| Gate 2 - source breakdown voltage | $\pm I_{G2S} = 10\text{ mA}$, $V_{G2S} = V_{DS} = 0$ | $\pm V_{(BR)G2SS}$ | 7 | | 10 | V |
| Gate 1 - source leakage current | $+ V_{G1S} = 5\text{ V}$, $V_{G2S} = V_{DS} = 0$ | $+ I_{G1SS}$ | | | 20 | nA |
| Gate 2 - source leakage current | $\pm V_{G2S} = 5\text{ V}$, $V_{G1S} = V_{DS} = 0$ | $\pm I_{G2SS}$ | | | 20 | nA |
| Drain - source operating current | $V_{DS} = V_{RG1} = 5\text{ V}$, $V_{G2S} = 4\text{ V}$, $R_{G1} = 56\text{ k}\Omega$ | I_{DSO} | 8 | 13 | 18 | mA |
| Gate 1 - source cut-off voltage | $V_{DS} = 5\text{ V}$, $V_{G2S} = 4$, $I_D = 20\text{ }\mu\text{A}$ | $V_{G1S(OFF)}$ | 0.5 | | 1.3 | V |
| Gate 2 - source cut-off voltage | $V_{DS} = V_{RG1} = 5\text{ V}$, $R_{G1} = 56\text{ k}\Omega$, $I_D = 20\text{ }\mu\text{A}$ | $V_{G2S(OFF)}$ | 0.8 | 1.0 | 1.4 | V |

Remark on improving intermodulation behavior:

By setting R_{G1} smaller than 56 k Ω , typical value of I_{DSO} will raise and improved intermodulation behavior will be performed.

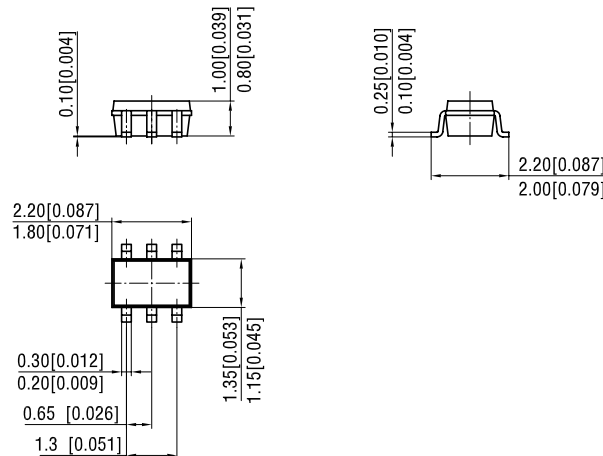
Electrical AC Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

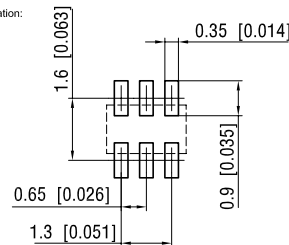
$V_{DS} = V_{RG1} = 5\text{ V}$, $V_{G2S} = 4\text{ V}$, $R_{G1} = 56\text{ k}\Omega$, $I_D = I_{DSO}$, $f = 1\text{ MHz}$

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|--------------------------|---|-----------------|------|------|-----|------------|
| Forward transadmittance | | $ Y_{21s} $ | 20 | 24 | 28 | mS |
| Gate 1 input capacitance | | C_{issg1} | | 1.7 | 2.1 | pF |
| Feedback capacitance | | C_{rss} | | 15 | 30 | fF |
| Output capacitance | | C_{oss} | | 0.9 | | pF |
| Power gain | $G_S = 2\text{ mS}$, $G_L = 0.5\text{ mS}$, $f = 200\text{ MHz}$ | G_{ps} | | 26 | | dB |
| | $G_S = 3.3\text{ mS}$, $G_L = 1\text{ mS}$, $f = 800\text{ MHz}$ | G_{ps} | 16.5 | 21 | | dB |
| AGC range | $V_{DS} = 5\text{ V}$, $V_{G2S} = 1\text{ to }4\text{ V}$, $f = 800\text{ MHz}$ | ΔG_{ps} | | 45 | | dB |
| Noise figure | $G_S = 2\text{ mS}$, $G_L = 0.5\text{ mS}$, $f = 200\text{ MHz}$ | F | | 1 | | dB |
| | $G_S = 3.3\text{ mS}$, $G_L = 1\text{ mS}$, $f = 800\text{ MHz}$ | F | | 1.3 | | dB |
| Cross modulation | Input level for $k = 1\%$ @ 0 dB AGC $f_w = 50\text{ MHz}$, $f_{unw} = 60\text{ MHz}$ | X_{mod} | 90 | | | dB μ V |
| | Input level for $k = 1\%$ @ 40 dB AGC $f_w = 50\text{ MHz}$, $f_{unw} = 60\text{ MHz}$ | X_{mod} | 100 | 105 | | dB μ V |

Package Dimensions in mm (Inches)



foot print recommendation:



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14280



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

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